



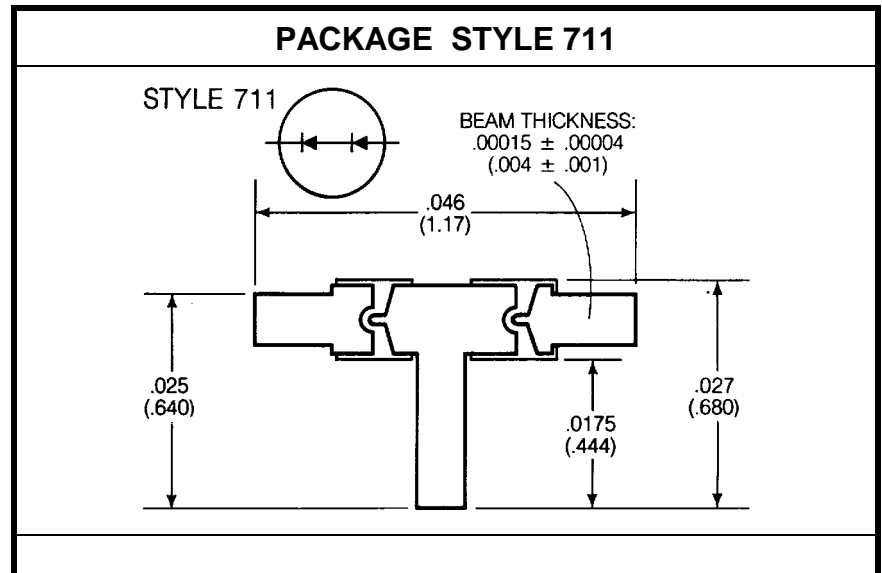
BEAM LEAD SCHOTTKY DIODE

DESCRIPTION:

The **ASI HSCH5531** is a Low Barrier Beam Lead Schottky Diode Designed for K-Band Mixer Applications.

MAXIMUM RATINGS

I_F	25 mA
V_R	4.0 V
P_{DISS}	150 mW @ $T_A = 25\text{ }^\circ\text{C}$
T_J	-65 $^\circ\text{C}$ to +175 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$



CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10\text{ }\mu\text{A}$	4.0			V
V_F	$I_F = 1.0\text{ mA}$			375	mV
ΔV_F	$I_F = 1.0\text{ mA}$			10	mV
I_R	$V_R = 1.0\text{ V}$			100	nA
R_D	$I_F = 5.0\text{ mA}$			20	Ω
ΔR_D	$I_F = 5.0\text{ mA}$			3.0	Ω
C_T	$V_R = 0\text{ V}$ $f = 1.0\text{ MHz}$			0.10	pF
ΔC_T	$V_R = 0\text{ V}$ $f = 1.0\text{ MHz}$			0.02	pF
TSS	Zero Bias, Zero Bias, $f = 10\text{ GHz}$		-46		dBm
γ	$P_{IN} = -30\text{ dBm}$ $R_L = 10\text{ M}\Omega$		17		mV/μW
R_V	Video Bandwidth = 2.0 MHz		1.4		MΩ